

SiC Schottky Barrier Diode

VOLTAGE RANGE: 650V

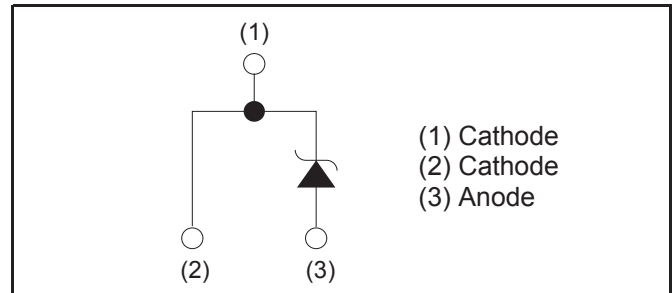
Features

- Shorter recovery time
- Reduced temperature dependence
- High-speed switching possible
- Silicon carbide epitaxial planer type

MECHANICAL DATA

- Case style: TO-220 molded plastic
- Mounting position: any

● Inner circuit



● Packaging specifications

Type	Packaging	Tube
	Basic ordering unit (pcs)	50
	Packing code	C
	Marking	SCS210AG

MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Reverse voltage (repetitive peak)	V_{RM}	650	V
Reverse voltage (DC)	V_R	650	V
Continuous forward current	I_F	10^{*1}	A
Surge no repetitive forward current	I_{FSM}	40^{*2}	A
		150^{*3}	A
		31^{*4}	A
Repetitive peak forward current	I_{FRM}	41^{*5}	A
Total power dissipation	P_D	78^{*6}	W
Junction temperature	T_j	175	°C
Range of storage temperature	T_{stg}	-55 to +175	°C

*1 $T_c=133^\circ\text{C}$ *2 $PW=8.3\text{ms}$ sinusoidal, $T_j=25^\circ\text{C}$ *3 $PW=10\mu\text{s}$ square, $T_j=25^\circ\text{C}$

*4 $PW=8.3\text{ms}$ sinusoidal, $T_j=150^\circ\text{C}$ *5 $T_c=100^\circ\text{C}$, $T_j=150^\circ\text{C}$, Duty cycle=10% *6 $T_c=25^\circ\text{C}$

RATINGS AND CHARACTERISTIC CURVES

Electrical Specification ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
DC blocking voltage	V_{DC}	$I_R=0.2\text{mA}$	600	-	-	V
Forward voltage	V_F	$I_F=10\text{A}, T_j=25^\circ\text{C}$	-	1.35	1.55	V
		$I_F=10\text{A}, T_j=150^\circ\text{C}$	-	1.55	-	V
		$I_F=10\text{A}, T_j=175^\circ\text{C}$	-	1.63	-	V
Reverse current	I_R	$V_R=600\text{V}, T_j=25^\circ\text{C}$	-	2	200	μA
		$V_R=600\text{V}, T_j=150^\circ\text{C}$	-	30	-	μA
		$V_R=600\text{V}, T_j=175^\circ\text{C}$	-	70	-	μA
Total capacitance	C	$V_R=1\text{V}, f=1\text{MHz}$	-	365	-	pF
		$V_R=600\text{V}, f=1\text{MHz}$	-	37	-	pF
Total capacitive charge	Qc	$V_R=400\text{V}, di/dt=350\text{A}/\mu\text{s}$	-	15	-	nC
Switching time	t_c	$V_R=400\text{V}, di/dt=350\text{A}/\mu\text{s}$	-	15	-	ns

● Thermal characteristics

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance	$R_{th(j-c)}$	-	-	1.6	1.9	$^\circ\text{C}/\text{W}$

RATINGS AND CHARACTERISTIC CURVES

Fig.1 $V_F - I_F$ Characteristics

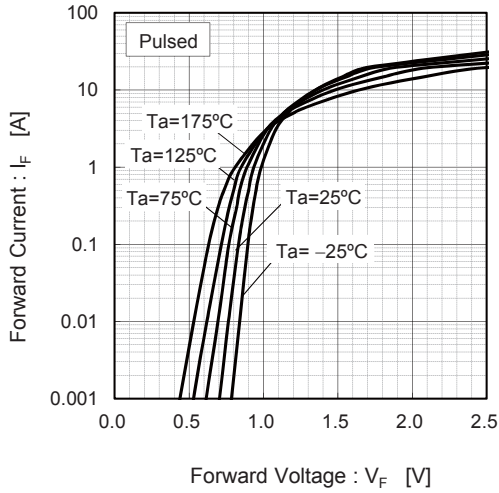


Fig.2 $V_F - I_F$ Characteristics

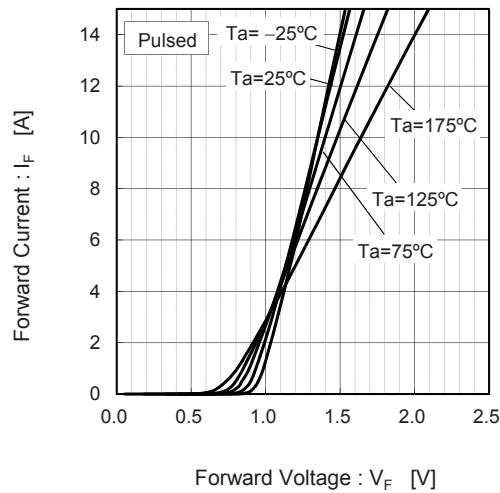


Fig.3 $V_R - I_R$ Characteristics

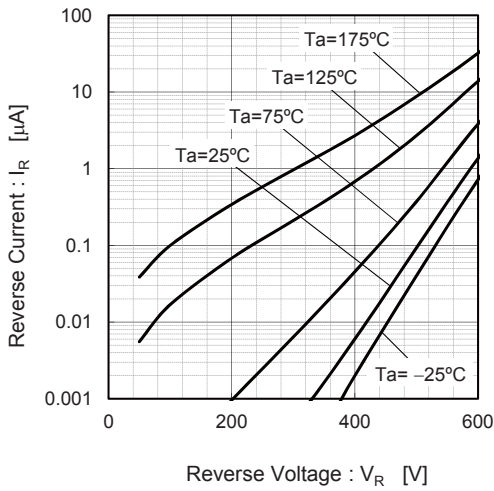


Fig.4 $V_R - C_t$ Characteristics

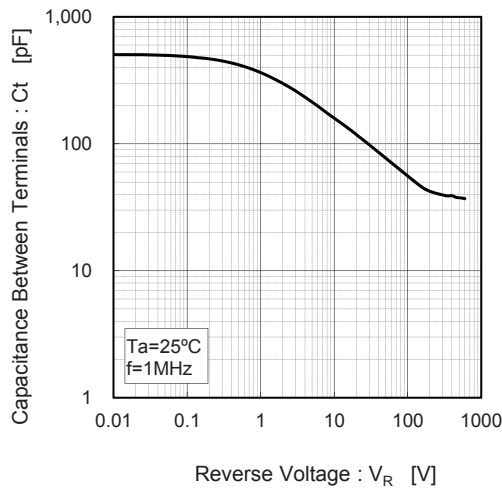


Fig.7 Derating Curve $I_p - T_c$

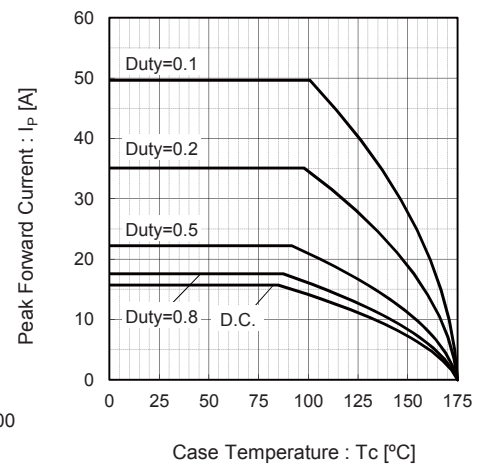


Fig.5 Thermal Resistance vs. Pulse Width

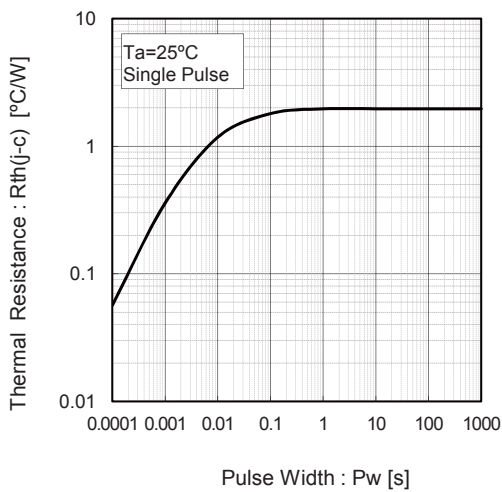


Fig.6 Power Dissipation

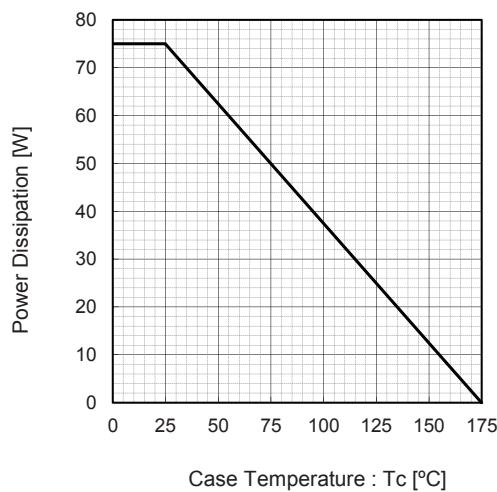


Fig.8 $I_o - P_f$ Characteristics

